

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) max}	I _D T _A = +25°C
-12V	$31m\Omega@V_{GS} = -4.5V$	-5.2A
-12V	45mΩ@ V _{GS} = -2.5V	-4.3A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- BLDC Motors
- Load Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

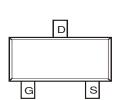
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.009 grams (Approximate)

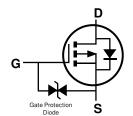




Top View



Pin Configuration



Internal Schematic

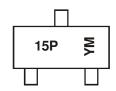
Ordering Information (Note 5)

Part Number	ber Compliance Case		Packaging	
DMP1045UQ-7	Automotive	SOT23	3,000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



15P = Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2013		•	~	20	17	20	18	20	19	20	20
Code	A ~ E		F		(G		Н				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-12	V		
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-4.0 -3.1	А
Continuous Drain Current (Note 6) V _{GS} = -2.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-3.3 -2.6	А
Continuous Drain Current (Note 7) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-5.2 -4.2	А
Continuous Drain Current (Note 7) V _{GS} = -2.5V	ID	-4.3 -3.4	А		
Maximum Continuous Body Diode Forward Current	I _S	-2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	-40	Α		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	168	°C/W
Total Power Dissipation (Note 7)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	99	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	14.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	•					
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -12V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	-0.55	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
			26	31		$V_{GS} = -4.5V$, $I_{D} = -4.0A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	31	45	mΩ	V _{GS} = -2.5V, I _D = -3.5A
			45	75		$V_{GS} = -1.8V, I_D = -2.7A$
Forward Transfer Admittance	Y _{fs}	_	12	_	S	$V_{DS} = -5V, I_{D} = -4A$
Diode Forward Voltage	V _{SD}	_	-0.6	_	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	1357	_	pF	101/11/
Output Capacitance	Coss	_	504	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	235	_	pF	1 - 1.01/11/2
Gate Resistance	Rg	_	14.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 9)						•
Total Gate Charge	Q_g		15.8	1	nC	
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -4A$
Gate-Drain Charge	Q_{gd}	_	3.9	_	nC]
Turn-On Delay Time	t _{D(ON)}	_	15.7	_	ns	
Turn-On Rise Time	t _R	_	23.3	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	91.2	_	ns	$R_L=2.5\Omega,R_G=3.0\Omega$
Turn-Off Fall Time	t _F	_	106.9		ns	1

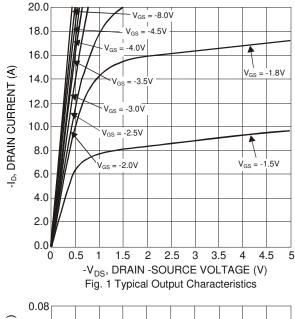
Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

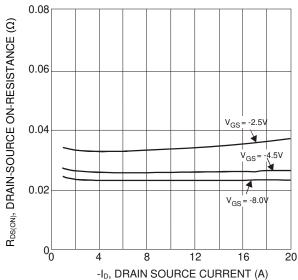
^{7.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate. 8 .Short duration pulse test used to minimize self-heating effect.

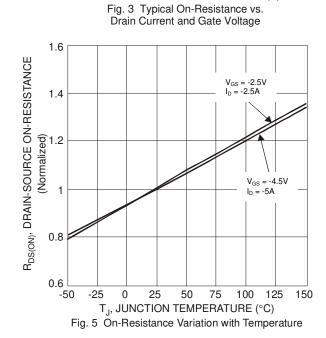
^{9.} Guaranteed by design. Not subject to production testing.

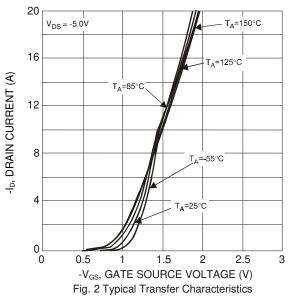


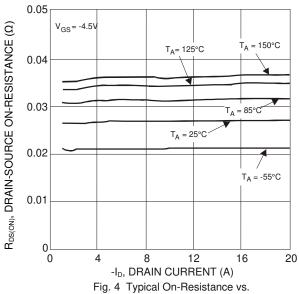












0.05 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) $\begin{aligned} V_{GS} &= -2.5V \\ I_D &= -2.5A \end{aligned}$ 0.04 0.03 $V_{GS} = -4.5V$ $I_D = -5A$ 0.02 0.01 0 -50 25 50 75 100 125 150 T,, JUNCTION TEMPERATURE (°C) Fig. 6 On-Resistance Variation with Temperature

Drain Current and Temperature



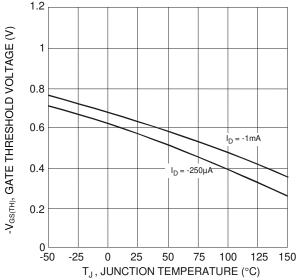


Fig. 7 Gate Threshold Variation vs. Junction Temperature

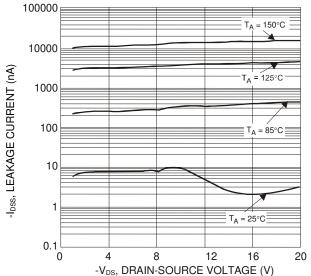


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

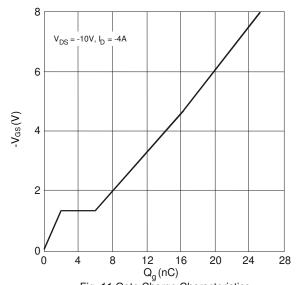
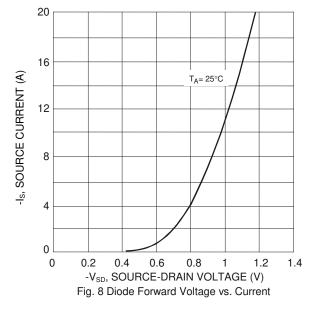
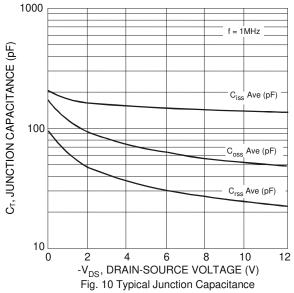


Fig. 11 Gate Charge Characteristics







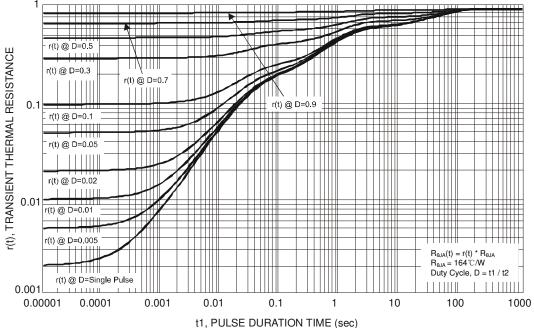


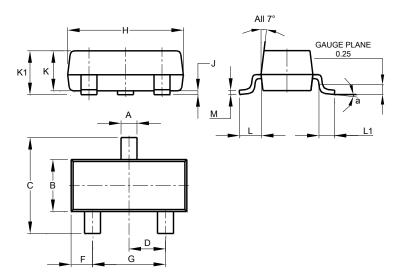
Fig. 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

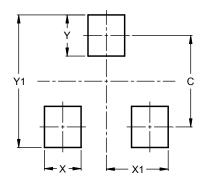


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
Y1	2.9



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